

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	72691	EEPROM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 07:31
L2	6891	(257/295,298,314-326).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:33
L3	2272	I1 and I2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:34
L4	7801	(tunnel channel) near oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:34
L5	877	(floating adj gate) with dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:59
L6	545	I4 and I5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:36
L7	146	I3 and I6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:37
L8	183	PBSG	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:43
L9	1	I7 and I8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:44

L10	5494	two near2 (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 07:42
L11	251	PBSG (phosphorous near boron near glass)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:43
L12	1	I7 and I11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:44
L13	10	I10 and I11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:55
L14	22995	TEOS tetraethyl adj orthosilicate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:29
L15	1	I5 and I11 and I14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:57
L16	5545	dielectric with (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:57
L17	695	(floating adj gate) with dielectric near5 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:04
L18	649	(floating adj gate) with dielectric near4 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:59
L19	535	(floating adj gate) with dielectric near3 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:59

L20	393	(floating adj gate) with dielectric near2 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 07:59
L21	201	(floating adj gate) with dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:03
L22	25	I21 and I14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:00
L23	0	I22 and I11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:00
L24	162	(floating adj gate) near5 dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:15
L25	127	(floating adj gate) near4 dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:04
L26	88	(floating adj gate) near3 dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:17
L27	44	(floating adj gate) near2 dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:11
L28	5	(floating adj gate) near dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:04
L29	39	I27 not I28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:11

L30	0	I24 and I11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:15
L31	649	(floating adj gate) and dielectric near (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:57
L32	1	I31 and I11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:16
L33	90	I31 and I14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:16
L34	0	I33 and two near gate adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 08:17
L35	10	I33 and two adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 08:22
L36	10	I35 and (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:56
L37	11	(silicone adj oxide) near5 I14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 08:33
L38	240	I14 with advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:11
L39	92	I14 near4 advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:12

L40	78	I14 near3 advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:12
L41	58	I14 near2 advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:12
L42	35	I14 near advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:16
L43	0	I24 and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:16
L44	4	I5 and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:16
L45	4	(floating adj gate) near3 dielectric and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:19
L46	4	(floating adj gate) and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:20
L47	4	I1 and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:20
L48	3	flash adj memory and I38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:28
L49	1646	silicon adj oxide near3 (TEOS tetraethyl adj orthosilicate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:30

L50	128	I1 and I49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:31
L51	0	I1 and (I49 with advantage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:32
L52	128	I1 and (I49 and advantage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:32
L53	112	I1 and (I49 and advantage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 12:39
L54	126	(ONO (oxide near nitride near oxide)) near5 advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 11:57
L55	7	I31 and I54	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 11:57
L56	4	I31 and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:12
L57	2	I24 and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 12:45
L58	10	I5 and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:03
L59	32	I1 and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:03

L60	26	59 not 58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:04
L61	13	l60 and (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:05
L62	0	(silicon adj oxide) near (side adj spacer sidewall) near5 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:13
L63	0	((silicon adj oxide) near (side adj spacer sidewall)) near5 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:13
L64	2	((silicon adj oxide) near (spacer sidewall)) near5 (ONO (oxide near nitride near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:14
L65	28	floating adj gate and ono and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:23
L66	27	l1 and floating adj gate and (silicon adj oxide) near (side adj spacer sidewall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/03 13:24
L67	2845	(sidewall side adj wall spacer) near3 (silicon adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:47
L68	190	l1 and l67	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:48
L69	153	l68 and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:48

L70	89	I69 and ono	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/03 13:48
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